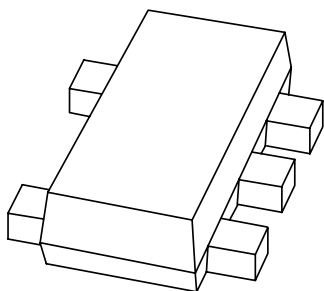


DATA SHEET



PESDxL4UW series

Low capacitance quadruple ESD
protection array

Product specification
Supersedes data of 2003 Aug 15

2004 Apr 06

Low capacitance quadruple ESD protection array

PESDxL4UW series

FEATURES

- Uni-directional ESD protection of four lines or bi-directional ESD protection of 3 lines
- Reverse standoff voltage: 3.3 and 5 V
- Low diode capacitance
- Ultra low leakage current
- Ultra small SOT665 surface mount package
- ESD protection >20 kV
- IEC 61000-4-2; level 4 (ESD); 15 kV (air) or 8 kV (contact).

APPLICATIONS

- Cellular handsets and accessories
- Portable electronics
- Computers and peripherals
- Communication systems
- Audio and video equipment.

MARKING

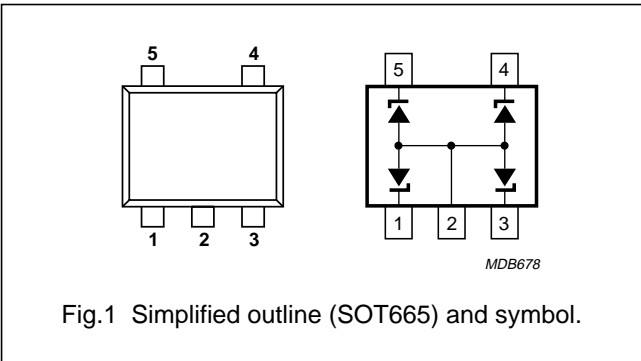
TYPE NUMBER	MARKING CODE
PESD3V3L4UW	A2
PESD5V0L4UW	A1

DESCRIPTION

Low capacitance quadruple ESD protection array in a five pad SOT665 ultra small plastic package designed to protect up to four transmission or data lines from ElectroStatic Discharge (ESD) damage.

PINNING

PIN	DESCRIPTION
1	cathode 1
2	common anode
3	cathode 2
4	cathode 3
5	cathode 4



ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PESD3V3L4UW	–	plastic surface mounted package; 5 leads	SOT665
PESD5V0L4UW			

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{pp}	peak pulse current	8/20 μ s; notes 1 and 2	–	3	A
	PESD3V3L4UW PESD5V0L4UW		–	2.5	A
P_{pp}	peak pulse power	8/20 μ s; notes 1 and 2	–	30	W
I_{FSM}	non-repetitive peak forward current	$t_p = 1$ ms; square pulse	–	3.5	A
I_{ZSM}	non-repetitive peak reverse current	$t_p = 1$ ms; square pulse			
	PESD3V3L4UW PESD5V0L4UW		–	0.9 0.8	A A
P_{tot}	total power dissipation	$T_{amb} = 25$ °C; note 3	–	250	mW
P_{ZSM}	non-repetitive peak reverse power dissipation	$t_p = 1$ ms; square pulse; see Fig.4	–	6	W
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
ESD	electrostatic discharge	IEC 61000-4-2 (contact discharge)	20	–	kV
		HBM MIL-Std 883	10	–	kV

Notes

1. Non-repetitive current pulse 8/20 μ s exponentially decaying waveform see Fig.5.
2. Pins 1, 3, 4 or 5 to pin 2.
3. Device mounted on standard printed-circuit board.

ESD standards compliance

IEC 61000-4-2, level 4 (ESD)	>15 kV (air); >8 kV (contact)
HBM MIL-Std 883, class 3	>4 kV

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	all diodes loaded	370	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point	one diode loaded; note 1	135	K/W
		all diodes loaded; note 1	125	K/W

Notes

1. Solder point of common anode (pin 2).

Low capacitance quadruple ESD protection array

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ELECTRICAL CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per diode						
V_F	forward voltage	$I_F = 200\text{ mA}$	–	1	1.2	V
V_{RWM}	reverse stand-off voltage					
	PESD3V3L4UW		–	–	3.3	V
	PESD5V0L4UW		–	–	5	V
I_{RM}	reverse leakage current					
	PESD3V3L4UW	$V_{RWM} = 3.3\text{ V}$	–	75	300	nA
	PESD5V0L4UW	$V_{RWM} = 5\text{ V}$	–	5	25	nA
$V_{(CL)R}$	clamping voltage					
	PESD3V3L4UW	$I_{pp} = 1\text{ A}$; note 1	–	–	8	V
		$I_{pp} = 3\text{ A}$; note 1	–	–	12	V
	PESD5V0L4UW	$I_{pp} = 1\text{ A}$; note 1	–	–	10	V
		$I_{pp} = 2.5\text{ A}$; note 1	–	–	13	V
V_{BR}	breakdown voltage	$I_Z = 1\text{ mA}$				
	PESD3V3L4UW		5.32	5.6	5.88	V
	PESD5V0L4UW		6.46	6.8	7.14	V
r_{diff}	differential resistance	$I_R = 1\text{ mA}$				
	PESD3V3L4UW		–	–	200	Ω
	PESD5V0L4UW		–	–	100	Ω
C_d	diode capacitance					
	PESD3V3L4UW	$f = 1\text{ MHz}$; $V_R = 0\text{ V}$	–	22	28	pF
		$f = 1\text{ MHz}$; $V_R = 5\text{ V}$	–	12	17	pF
	PESD5V0L4UW	$f = 1\text{ MHz}$; $V_R = 0\text{ V}$	–	16	19	pF
		$f = 1\text{ MHz}$; $V_R = 5\text{ V}$	–	8	11	pF

Notes

1. Pins 1, 3, 4 or 5 to pin 2.

Low capacitance quadruple ESD protection array

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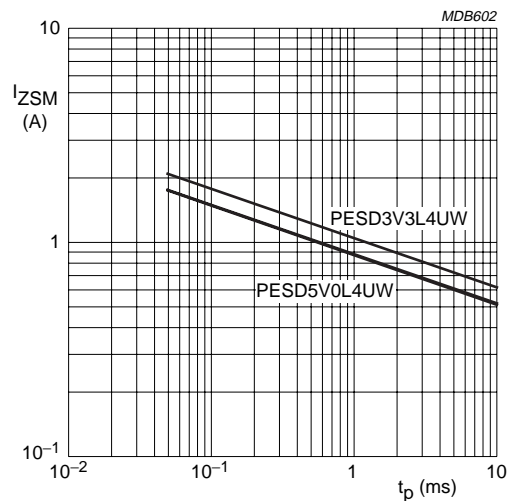
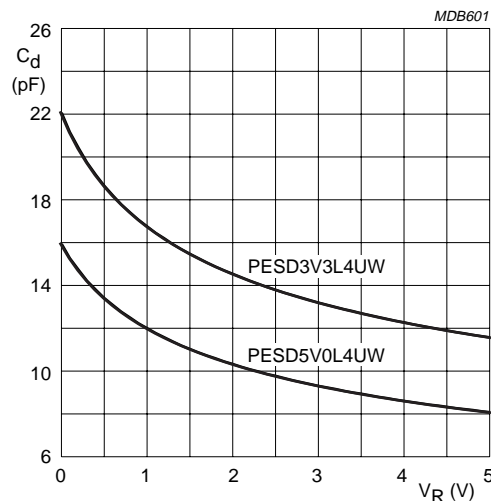
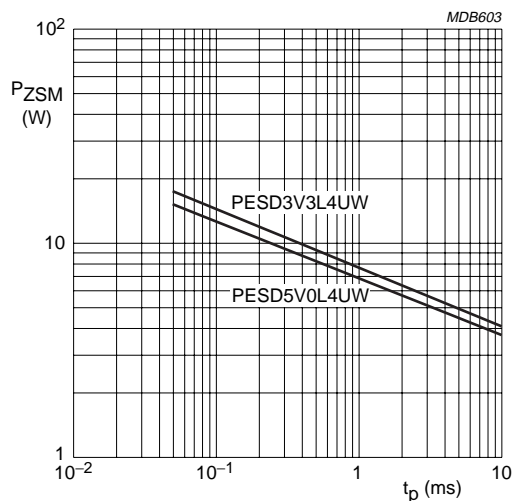


Fig.2 Non-repetitive peak reverse current as a function of pulse time (square pulse).



$T_j = 25\text{ }^{\circ}\text{C}$; $f = 1\text{ MHz}$.

Fig.3 Diode capacitance as a function of reverse voltage; typical values.



$P_{ZSM} = V_{ZSM} \times I_{ZSM}$.
 V_{ZSM} is the non-repetitive peak reverse voltage at I_{ZSM} .

Fig.4 Maximum non-repetitive peak reverse power dissipation as a function of pulse duration (square pulse).

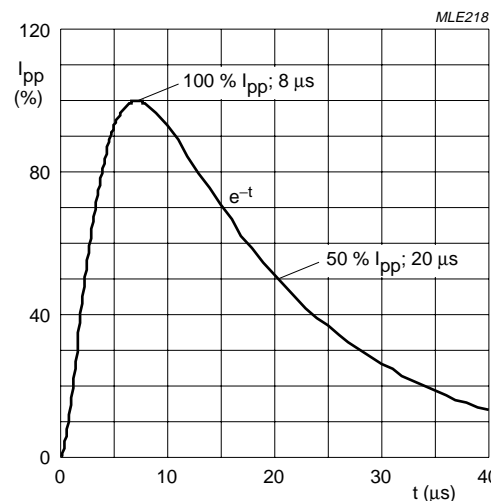


Fig.5 8/20 μs pulse waveform according to IEC 61000-4-5.

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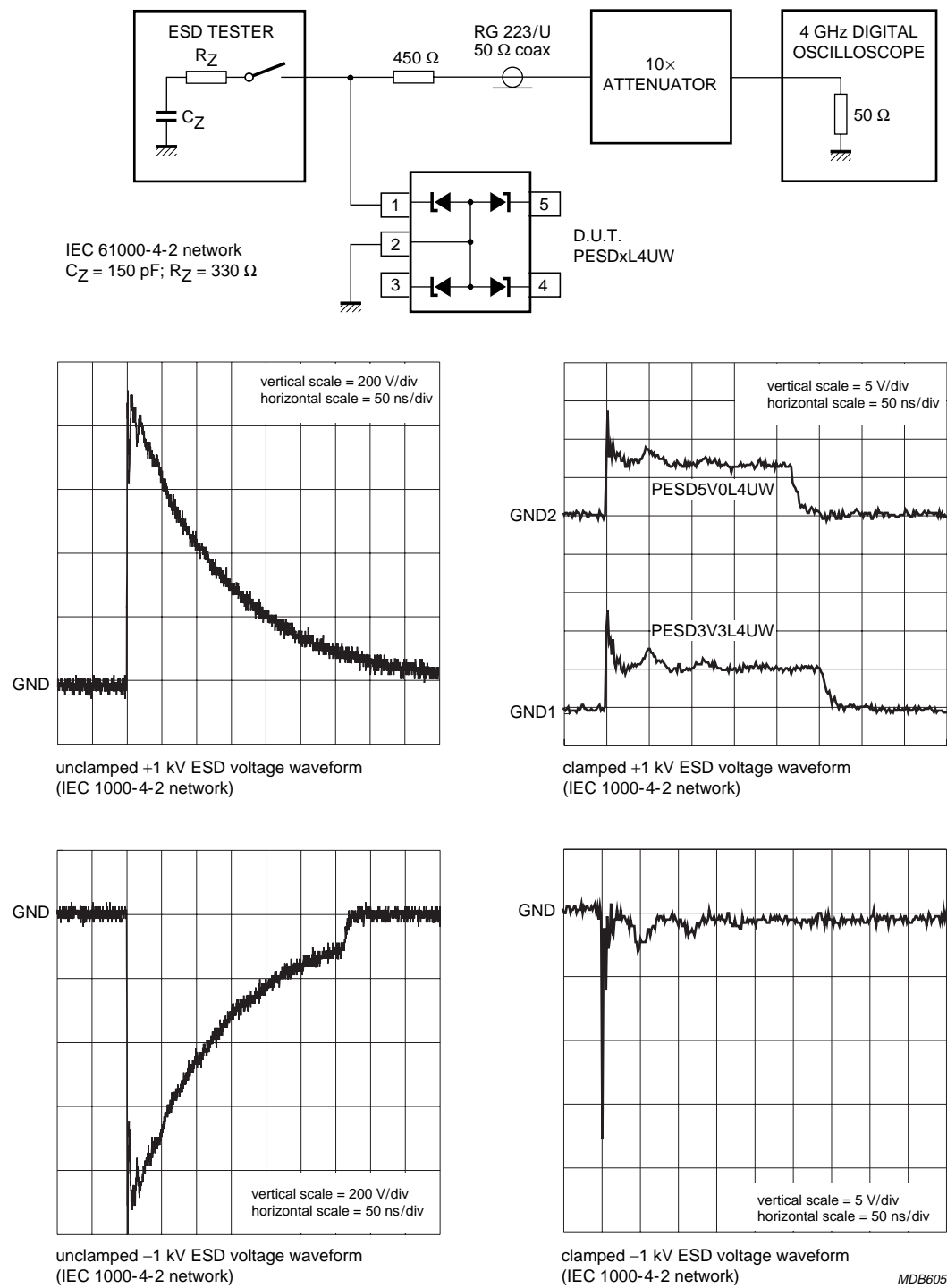


Fig.6 ESD clamping test set-up and waveforms.

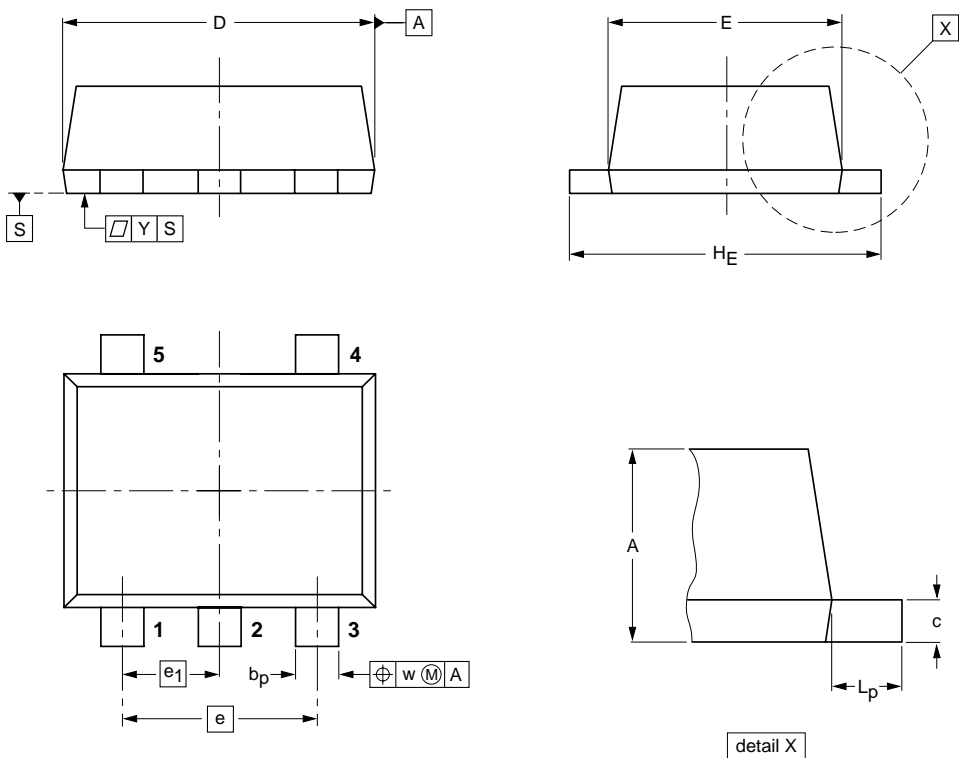
Low capacitance quadruple ESD
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PACKAGE OUTLINE

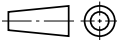
Plastic surface mounted package; 5 leads

SOT665



DIMENSIONS (mm are the original dimensions)

UNIT	A	b _p	c	D	E	e	e ₁	H _E	L _p	w	y
mm	0.6 0.5	0.27 0.17	0.18 0.08	1.7 1.5	1.3 1.1	1.0	0.5	1.7 1.5	0.3 0.1	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT665						01-01-04 01-08-27

Low capacitance quadruple ESD protection array

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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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